

SOT89 NPN SILICON PLANAR HIGH VOLTAGE TRANSISTOR

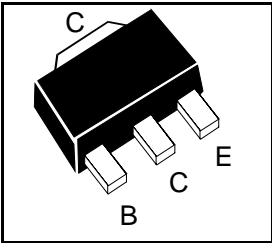
FCX458

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FEATURES

- * 400 Volt V_{CE0}
- * P_{tot} = 1 Watt

COMPLEMENTARY TYPE – FCX558
PARTMARKING DETAIL – N58



ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	V_{CBO}	400	V
Collector-Emitter Voltage	V_{CEO}	400	V
Emitter-Base Voltage	V_{EBO}	5	V
Continuous Collector Current	I_C	225	mA
Peak Pulse Current	I_{CM}	500	mA
Power Dissipation at $T_{amb}=25^{\circ}C$	P_{tot}	1	W
Operating and Storage Temperature Range	T_j, T_{stg}	-65 to +150	$^{\circ}C$

ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Breakdown Voltages	$V_{(BR)CBO}$	400		V	$I_C=100\mu A$
	$V_{CEO(sus)}$	400		V	$I_C=10mA^*$
	$V_{(BR)EBO}$	5		V	$I_E=100\mu A$
Collector Cut-Off Currents	I_{CBO}		100	nA	$V_{CB}=320V$
	I_{CES}		100	nA	$V_{CE}=320V$
Emitter Cut-Off Current	I_{EBO}		100	nA	$V_{EB}=4V$
Emitter Saturation Voltages	$V_{CE(sat)}$		0.2 0.5	V V	$I_C=20mA, I_B=2mA^*$ $I_C=50mA, I_B=6mA^*$
	$V_{BE(sat)}$		0.9	V	$I_C=50mA, I_B=5mA^*$
Base-Emitter Turn On Voltage	$V_{BE(on)}$		0.9	V	$I_C=50mA, V_{CE}=10V^*$
Static Forward Current Transfer Ratio	h_{FE}	100 100 15	300		$I_C=1mA, V_{CE}=10V$ $I_C=50mA, V_{CE}=10V^*$ $I_C=100mA, V_{CE}=10V^{**}$
Transition Frequency	f_T	50		MHz	$I_C=10mA, V_{CE}=20V$ $f=20MHz$
Collector-Base Breakdown Voltage	C_{obo}		5	pF	$V_{CB}=20V, f=1MHz$
Switching times	t_{on}	135 Typical		ns	$I_C=50mA, V_C=100V$ $I_{B1}=5mA, I_{B2}=-10mA$
	t_{off}	2260 Typical		ns	

*Measured under pulsed conditions. Pulse width=300 μs . Duty cycle $\leq 2\%$
Spice parameter data is available upon request for this device
For typical characteristics graphs see FMMT458 datasheet